



74LCX540

LOW VOLTAGE CMOS OCTAL BUS BUFFER (3-STATE) WITH 5V TOLERANT INPUTS AND OUTPUTS

- 5V TOLERANT INPUTS AND OUTPUTS
- HIGH SPEED:
 $t_{PD} = 8.0 \text{ ns (MAX.) at } V_{CC} = 3V$
- POWER DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 24\text{mA (MIN) at } V_{CC} = 3V$
- PCI BUS LEVELS GUARANTEED AT 24 mA
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC(OPR)} = 2.0V \text{ to } 3.6V \text{ (1.5V Data Retention)}$
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 540
- LATCH-UP PERFORMANCE EXCEEDS 500mA (JESD 17)
- ESD PERFORMANCE:
 $HBM > 2000V \text{ (MIL STD 883 method 3015);}$
 $MM > 200V$

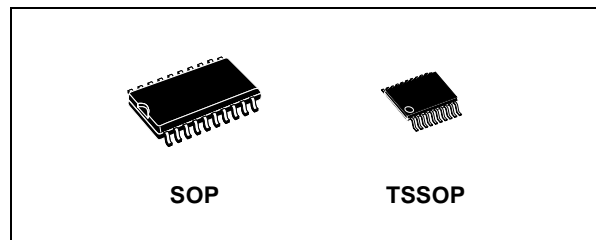


Table 1: Order Codes

PACKAGE	T & R
SOP	74LCX540MTR
TSSOP	74LCX540TTR

The 3 STATE control gate operates as two input AND such that if either G1 and G2 are high, all eight outputs are in the high impedance state. In order to enhance PC board layout the 74LCX540 offers a pinout having inputs and outputs on opposite sides of the package.

It has same speed performance at 3.3V than 5V AC/ACT family, combined with a lower power consumption.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

DESCRIPTION

The 74LCX540 is a low voltage CMOS OCTAL BUS BUFFER (INVERTED) fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. It is ideal for low power and high speed 3.3V applications; it can be interfaced to 5V signal environment for both inputs and outputs.

Figure 1: Pin Connection And IEC Logic Symbols

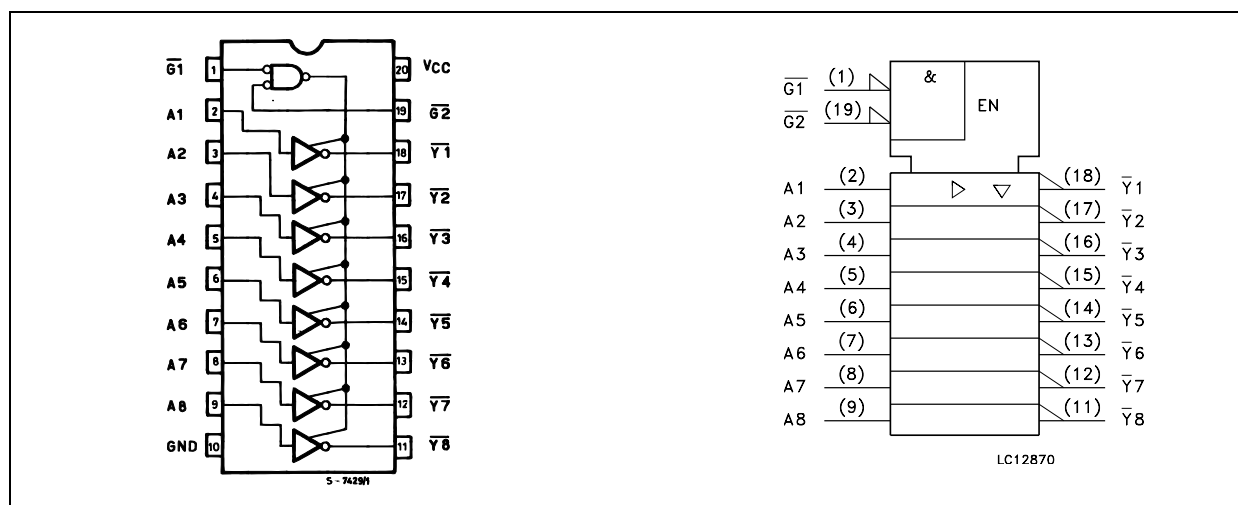


Figure 2: Input And Output Equivalent Circuit

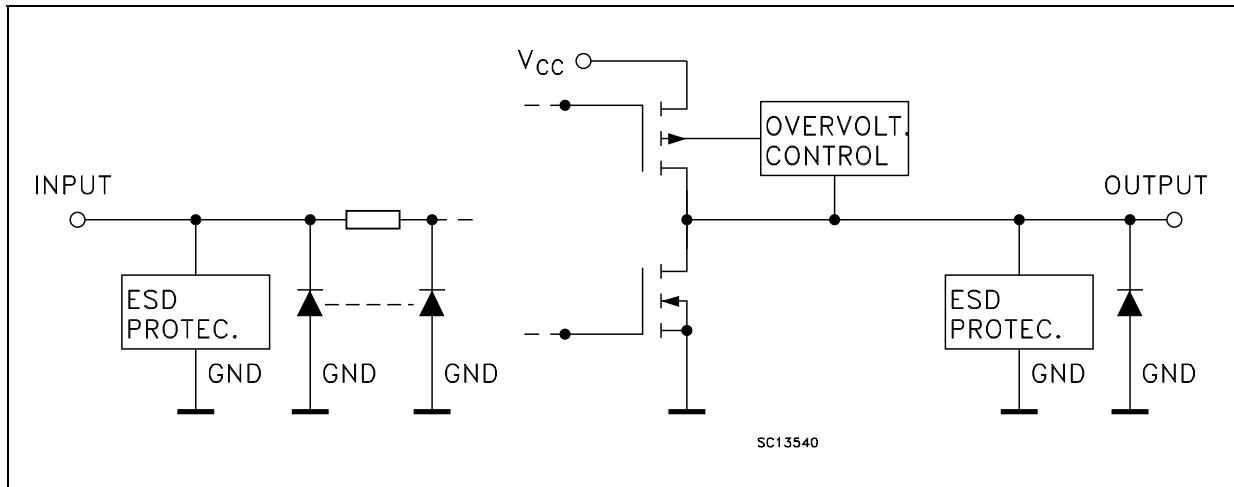


Table 2: Pin Description

PIN N°	SYMBOL	NAME AND FUNCTION
1, 19	G1, G2	Output Enable Inputs
2, 3, 4, 5, 6, 7, 8, 9	A1 to A8	Data Inputs
18, 17, 16, 15, 14, 13, 12, 11	Y1 to Y8	Data Outputs
10	GND	Ground (0V)
20	V _{CC}	Positive Supply Voltage

Table 3: Truth Table

INPUT			OUTPUT
G1	G2	A _n	Y _n
H	X	X	Z
X	H	X	Z
L	L	H	L
L	L	L	H

X : Don't Care
Z : High Impedance

Table 4: Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
V _O	DC Output Voltage (OFF State)	-0.5 to +7.0	V
V _O	DC Output Voltage (High or Low State) (note 1)	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 50	mA
I _{OK}	DC Output Diode Current (note 2)	- 50	mA
I _O	DC Output Current	± 50	mA
I _{CC}	DC Supply Current per Supply Pin	± 100	mA
I _{GND}	DC Ground Current per Supply Pin	± 100	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

- 1) I_O absolute maximum rating must be observed
- 2) V_O < GND

Table 5: Recommended Operating Conditions

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage (note 1)	2.0 to 3.6	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage (OFF State)	0 to 5.5	V
V_O	Output Voltage (High or Low State)	0 to V_{CC}	V
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 3.0$ to $3.6V$)	± 24	mA
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 2.7V$)	± 12	mA
T_{op}	Operating Temperature	-55 to 125	$^{\circ}C$
dt/dv	Input Rise and Fall Time (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.5V to 3.6V

2) V_{IN} from 0.8V to 2V at $V_{CC} = 3.0V$

Table 6: DC Specifications

Symbol	Parameter	Test Condition		Value				Unit
		V_{CC} (V)		-40 to 85 $^{\circ}C$		-55 to 125 $^{\circ}C$		
				Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.7 to 3.6		2.0		2.0		V
V_{IL}	Low Level Input Voltage				0.8		0.8	V
V_{OH}	High Level Output Voltage	2.7 to 3.6	$I_O = -100 \mu A$	$V_{CC} - 0.2$		$V_{CC} - 0.2$		V
		2.7	$I_O = -12 mA$	2.2		2.2		
		3.0	$I_O = -18 mA$	2.4		2.4		
			$I_O = -24 mA$	2.2		2.2		
V_{OL}	Low Level Output Voltage	2.7 to 3.6	$I_O = 100 \mu A$		0.2		0.2	V
		2.7	$I_O = 12 mA$		0.4		0.4	
		3.0	$I_O = 16 mA$		0.4		0.4	
			$I_O = 24 mA$		0.55		0.55	
I_I	Input Leakage Current	2.7 to 3.6	$V_I = 0$ to $5.5V$		± 5		± 5	μA
I_{off}	Power Off Leakage Current	0	V_I or $V_O = 5.5V$		10		10	μA
I_{OZ}	High Impedance Output Leakage Current	2.7 to 3.6	$V_I = V_{IH}$ or V_{IL} $V_O = 0$ to V_{CC}		± 5		± 5	μA
I_{CC}	Quiescent Supply Current	2.7 to 3.6	$V_I = V_{CC}$ or GND		10		10	μA
			V_I or $V_O = 3.6$ to $5.5V$		± 10		± 10	
ΔI_{CC}	I_{CC} incr. per Input	2.7 to 3.6	$V_{IH} = V_{CC} - 0.6V$		500		500	μA

Table 7: Dynamic Switching Characteristics

Symbol	Parameter	Test Condition		Value			Unit
		V _{CC} (V)		T _A = 25 °C			
				Min.	Typ.	Max.	
V _{OLP}	Dynamic Low Level Quiet Output (note 1)	3.3	C _L = 50pF V _{IL} = 0V, V _{IH} = 3.3V		0.8		V
V _{OLV}					-0.8		

1) Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining output is measured in the LOW state.

Table 8: AC Electrical Characteristics

Symbol	Parameter	Test Condition				Value				Unit
		V _{CC} (V)	C _L (pF)	R _L (Ω)	t _s = t _r (ns)	-40 to 85 °C		-55 to 125 °C		
						Min.	Max.	Min.	Max.	
t _{PLH} t _{PHL}	Propagation Delay Time	2.7	50	500	2.5	1.5	9.0	1.5	9.0	ns
		3.0 to 3.6				1.5	8.0	1.5	8.0	
t _{PZL} t _{PZH}	Output Enable Time	2.7	50	500	2.5	1.5	9.5	1.5	9.5	ns
		3.0 to 3.6				1.5	8.5	1.5	8.5	
t _{PLZ} t _{PHZ}	Output Disable Time	2.7	50	500	2.5	1.5	8.5	1.5	8.5	ns
		3.0 to 3.6				1.5	7.5	1.5	7.5	
t _{OSLH} t _{OSSL}	Output To Output Skew Time (note1, 2)	3.0 to 3.6	50	500	2.5	1.0		1.0	ns	

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW (t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSSL} = |t_{PHLm} - t_{PHLn}|)

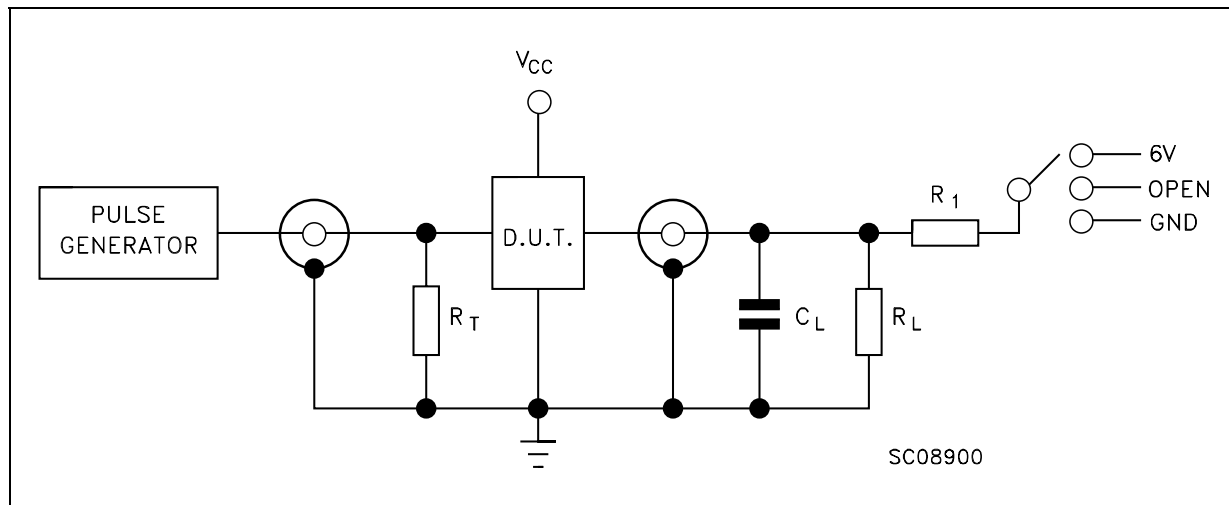
2) Parameter guaranteed by design

Table 9: Capacitive Characteristics

Symbol	Parameter	Test Condition		Value			Unit
		V _{CC} (V)		T _A = 25 °C			
				Min.	Typ.	Max.	
C _{IN}	Input Capacitance	3.3	V _{IN} = 0 to V _{CC}		6		pF
C _{OUT}	Output Capacitance	3.3	V _{IN} = 0 to V _{CC}		12		pF
C _{PD}	Power Dissipation Capacitance (note 1)	3.3	f _{IN} = 10MHz V _{IN} = 0 or V _{CC}		25		pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(opr)} = C_{PD} × V_{CC} × f_{IN} + I_{CC/8} (per buffer)

Figure 3: Test Circuit



TEST	SWITCH
t_{PLH} , t_{PHL}	Open
t_{PZL} , t_{PLZ}	6V
t_{PZH} , t_{PHZ}	GND

$C_L = 50$ pF or equivalent (includes jig and probe capacitance)

$R_L = R_1 = 500\Omega$ or equivalent

$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

Figure 4: Waveform - Propagation Delays ($f=1$ MHz; 50% duty cycle)

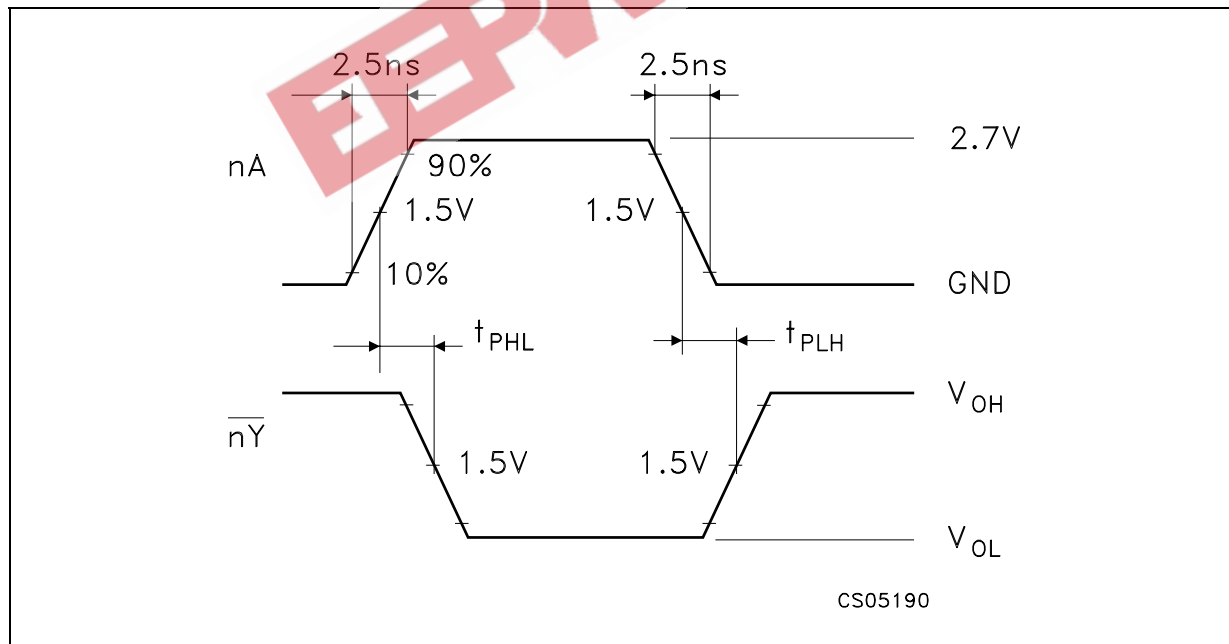
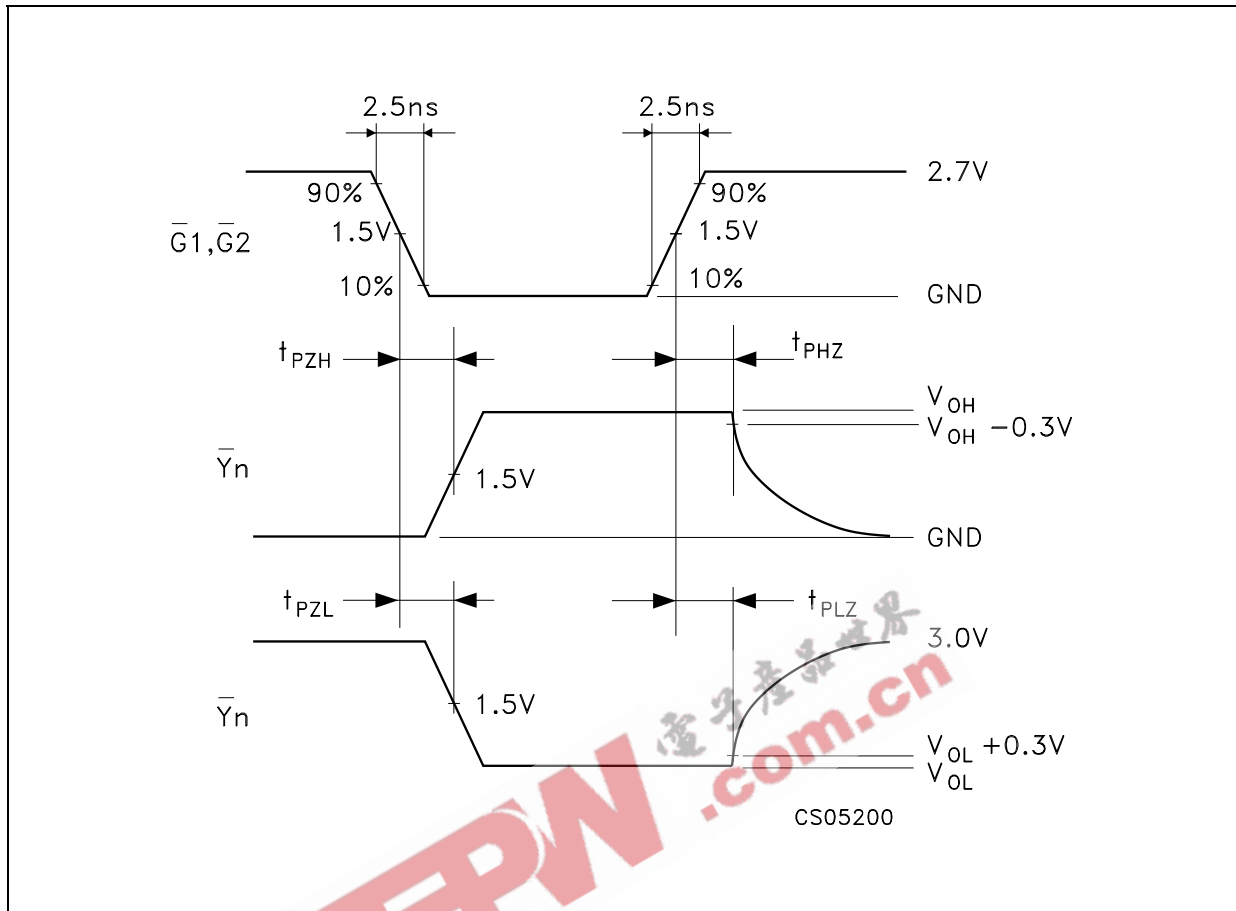
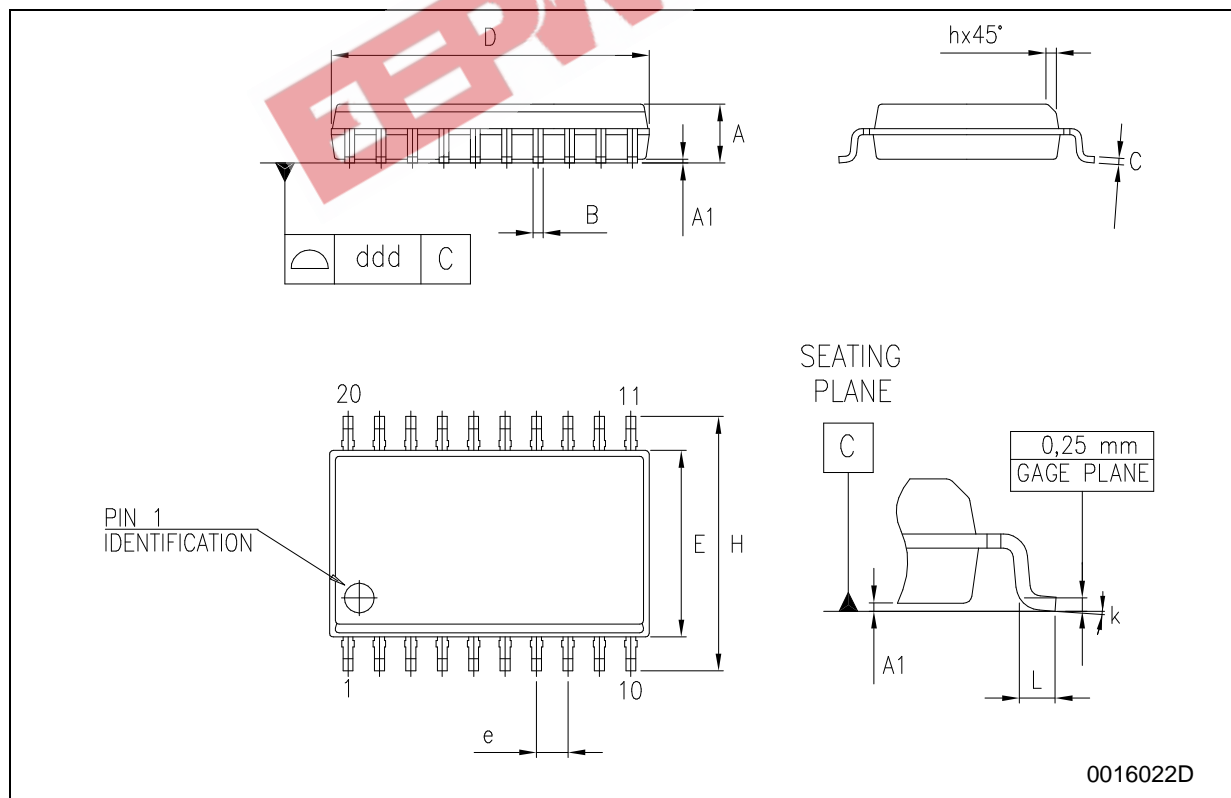


Figure 5: Waveform - Output Enable And Disable Time (f=1MHz; 50% duty cycle)



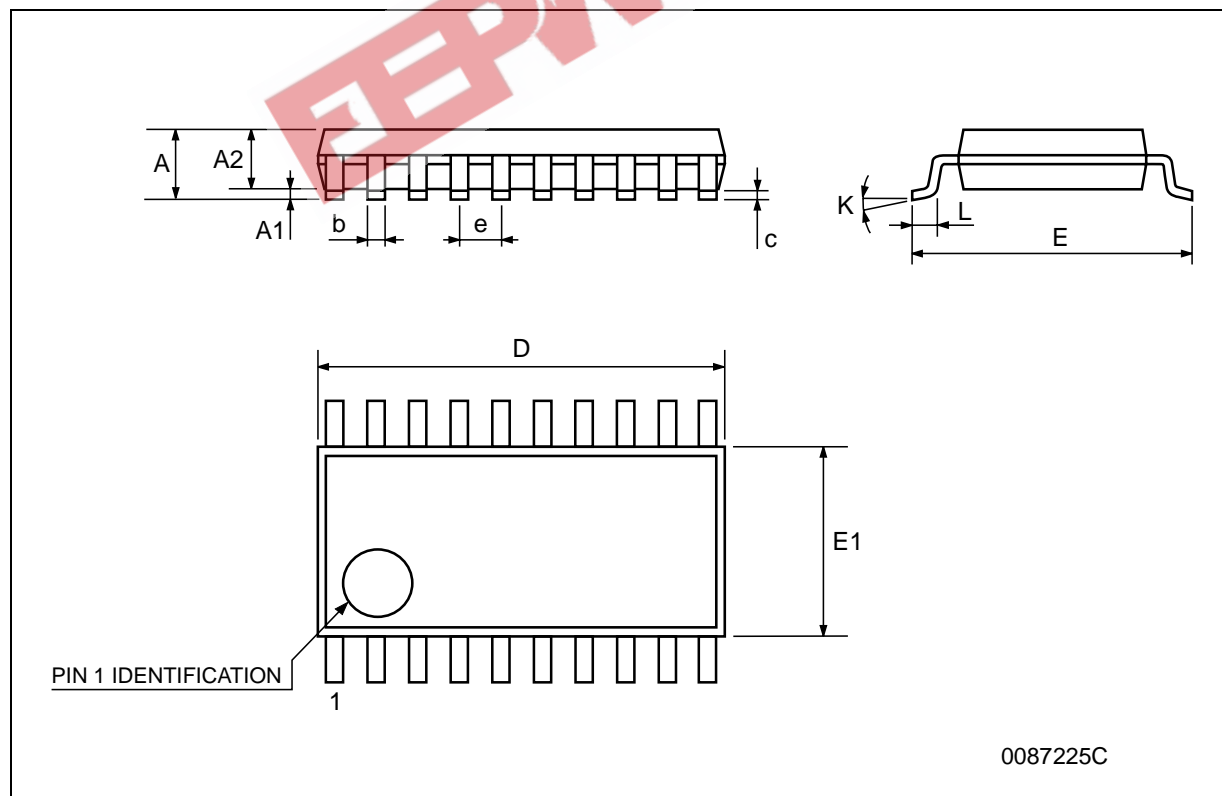
SO-20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.35		2.65	0.093		0.104
A1	0.1		0.30	0.004		0.012
B	0.33		0.51	0.013		0.020
C	0.23		0.32	0.009		0.013
D	12.60		13.00	0.496		0.512
E	7.4		7.6	0.291		0.299
e		1.27			0.050	
H	10.00		10.65	0.394		0.419
h	0.25		0.75	0.010		0.030
L	0.4		1.27	0.016		0.050
k	0°		8°	0°		8°
ddd			0.100			0.004



TSSOP20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0079
D	6.4	6.5	6.6	0.252	0.256	0.260
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



Tape & Reel SO-20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			30.4			1.197
Ao	10.8		11	0.425		0.433
Bo	13.2		13.4	0.520		0.528
Ko	3.1		3.3	0.122		0.130
Po	3.9		4.1	0.153		0.161
P	11.9		12.1	0.468		0.476



Tape & Reel TSSOP20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			22.4			0.882
Ao	6.8		7	0.268		0.276
Bo	6.9		7.1	0.272		0.280
Ko	1.7		1.9	0.067		0.075
Po	3.9		4.1	0.153		0.161
P	11.9		12.1	0.468		0.476

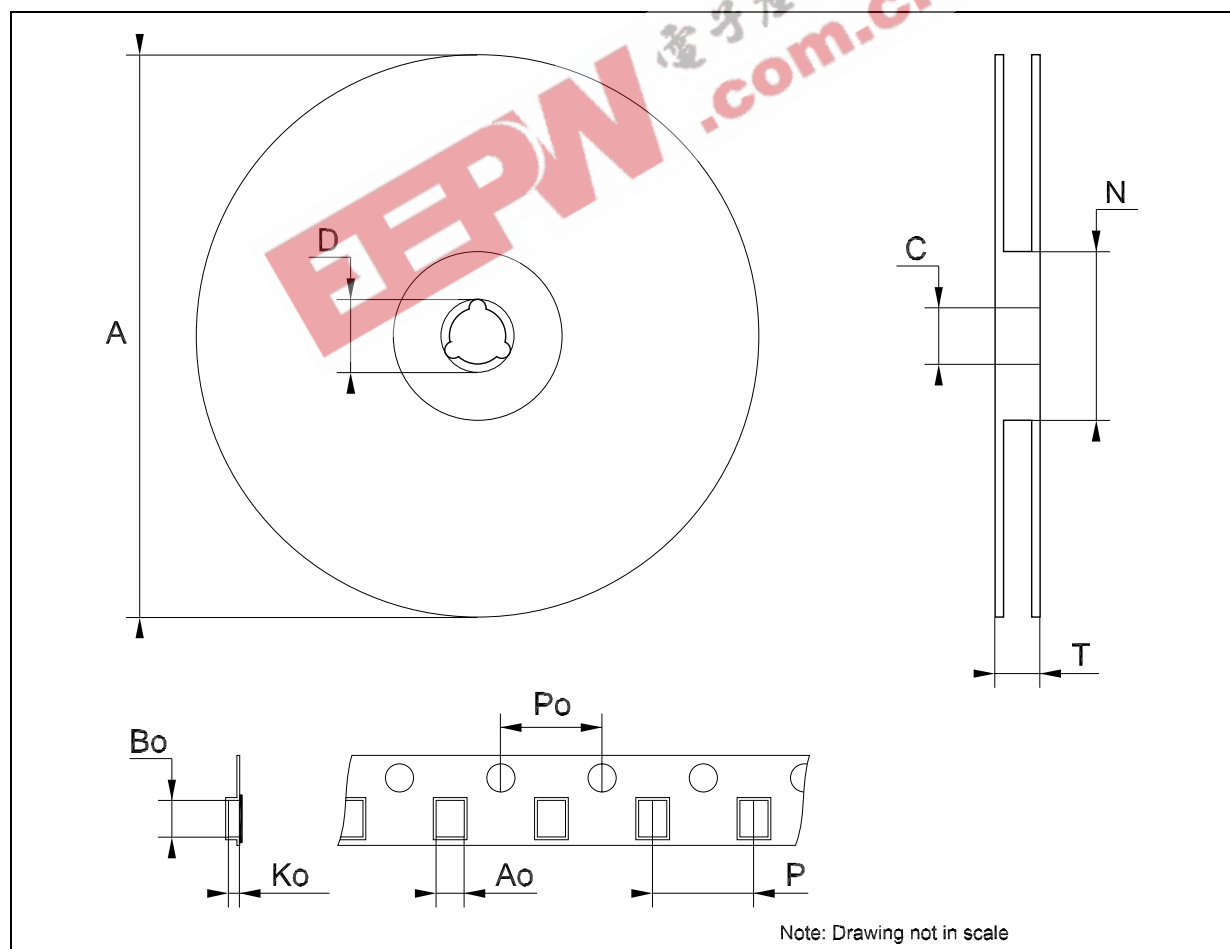


Table 10: Revision History

Date	Revision	Description of Changes
15-Sep-2004	3	Ordering Codes Revision - pag. 1.

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